

**A HIGH DOPANT CONCENTRATION DIFFUSED RESISTOR
AND METHOD OF MANUFACTURE THEREFOR**

ABSTRACT OF THE DISCLOSURE

The present invention provides a high dopant concentration diffused resistor, a method of manufacture therefor, and an integrated circuit including the same. In one embodiment of the invention, the high dopant concentration diffused resistor includes a doped tub located over a semiconductor substrate and a doped resistor region located in the doped tub, the doped resistor region forming a junction within the doped tub. In a related embodiment, the high dopant concentration diffused resistor further includes first and second terminals each contacting the doped tub and the doped resistor region, wherein the first and second terminals cause the doped tub and doped resistor region to have a zero potential difference at any point across the junction when a voltage is applied to the first and second terminals.